

/ Revised record

[illegible]

/ Descriptions

SOD-123

Schottky Diode in a SOD-123 Plastic Package.

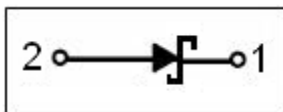
/ Features

Metal silicon junction, majority carrier conduction. Guarding for overvoltage protection.Low power loss, high efficiency. High current capability. low forward voltage drop. High surge capability. For use in low voltage, high frequency inverters,free wheeling, and polarity protection applications.HF Product.

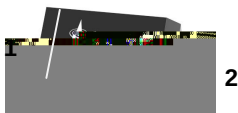
/ Applications

General purpose.

/ Equivalent Circuit



/ Pinning

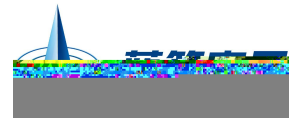


PIN1:Cathode

PIN2:Anode

/ Marking

Type number	Marking code
BAT54W	L4



Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	30	V
Maximum Average Forward Current	I_O	0.2	A
Peak Forward Surge Current, 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I_{FSM}	13	A
Typical Thermal Resistance	$R_{\theta JA}$	435	$^{\circ}C/W$
Typical Junction Capacitance at $V_R=0V$, $f=1MHz$	C_j	60	pF
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +125	$^{\circ}C$

Parameter	Symbol	Test Conditions	Rating			Unit
			Min	Typ	Max	
Maximum Instantaneous Forward Voltage	V_F	$I_F=0.001A$			0.32	V

/ Electrical Characteristic Curve

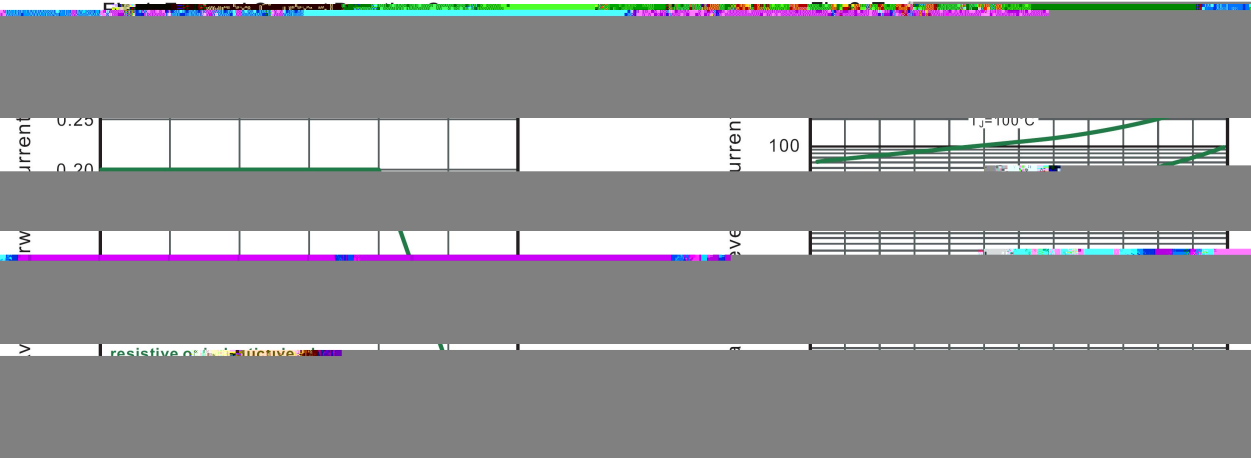
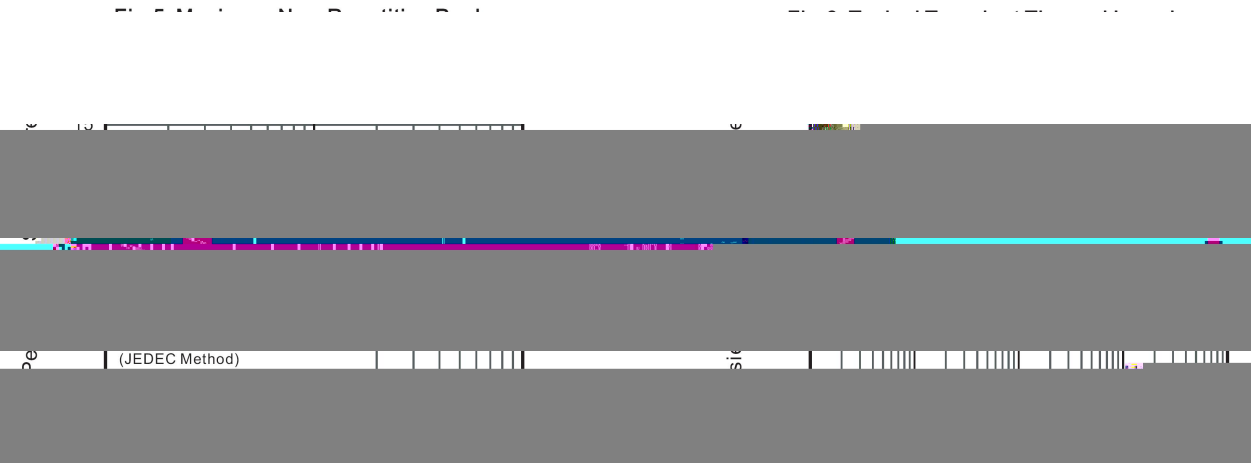
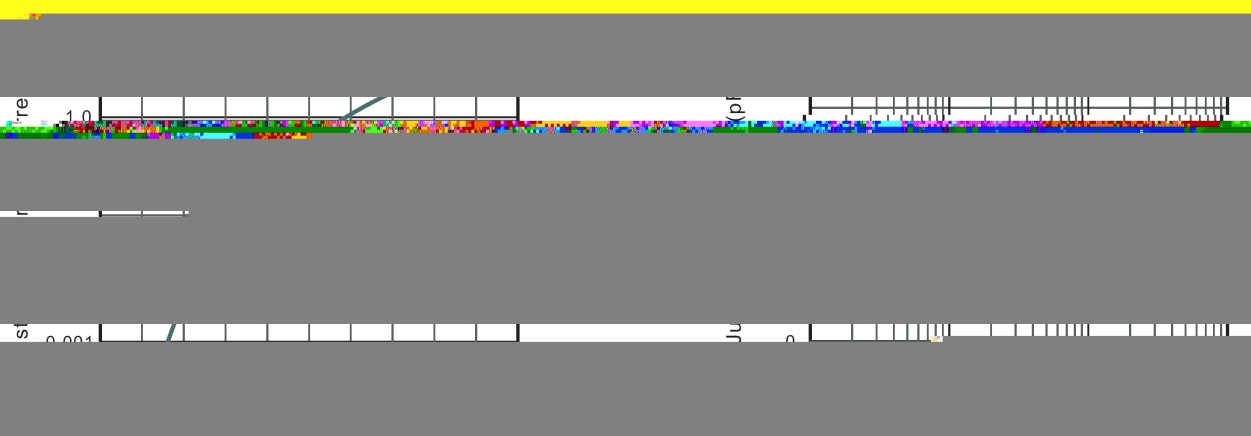
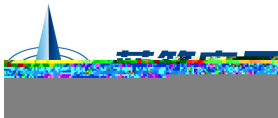


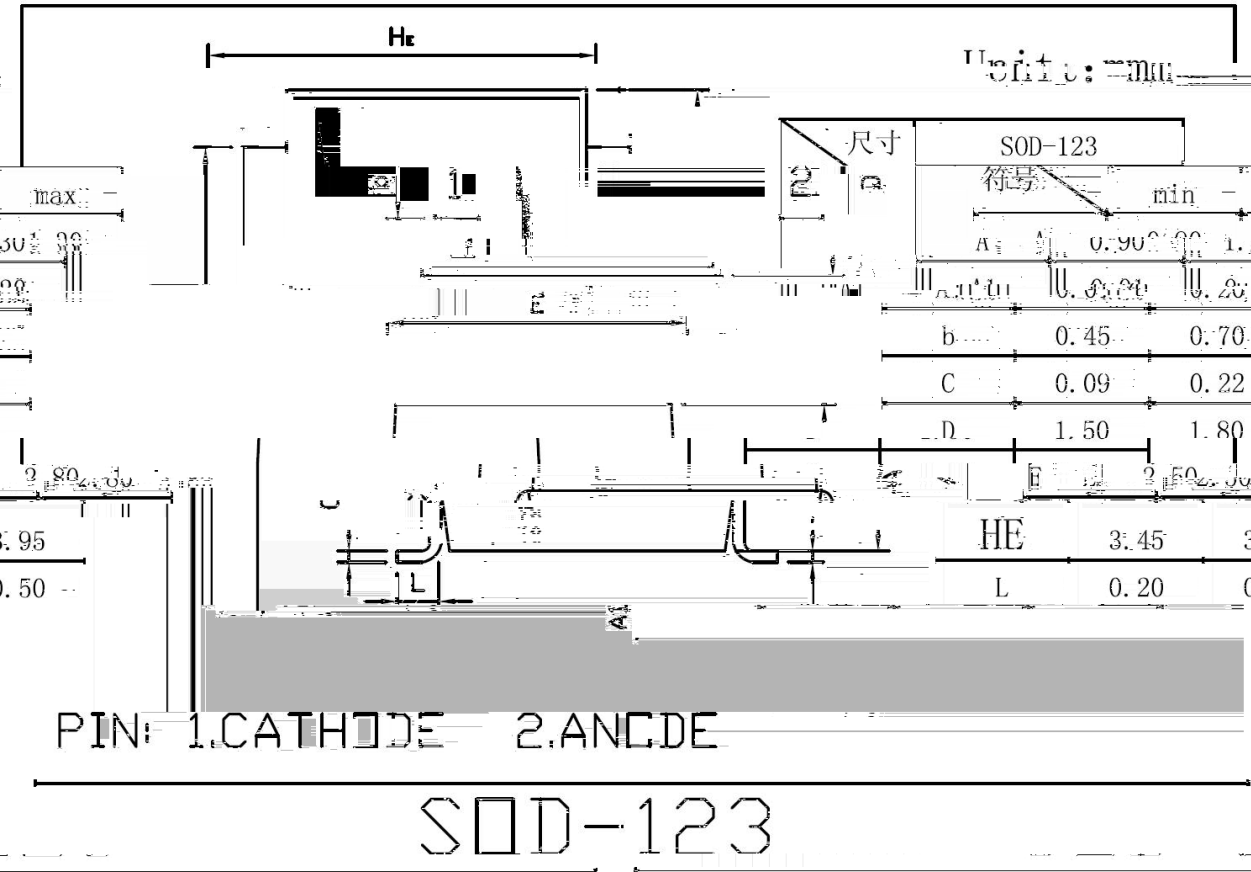
Fig.4 Typical Forward Characteristics

Fig.4 Typical Junction Capacitance





/ Package Dimensions



/ Marking Instructions



L4

Note:

L4 : Product Type



() /

Note:

- | | | | |
|---|---------------|-------------|--|
| 1 | 150 ~ 180 | 60 ~ 90sec; | 1.Preheating:150~180°C, Time:60~90sec. |
| 2 | 245±5 | 5±0.5sec; | 2.Peak Temp.:245±5°C, Duration:5±0.5sec. |
| 3 | 2 ~ 10°C/sec. | | 3. Cooling Speed: 2~10°C/sec. |

/ Resistance to Soldering Heat Test Con/ ng ↓

C